

## Silicon Photodiode

### OSD18-254



## Description

The OSD18-254 is high sensitivity silicon photodiode for Monochromatic light with interference filter window. It Has a peak sensitivity wavelength at 254nm.

## Features

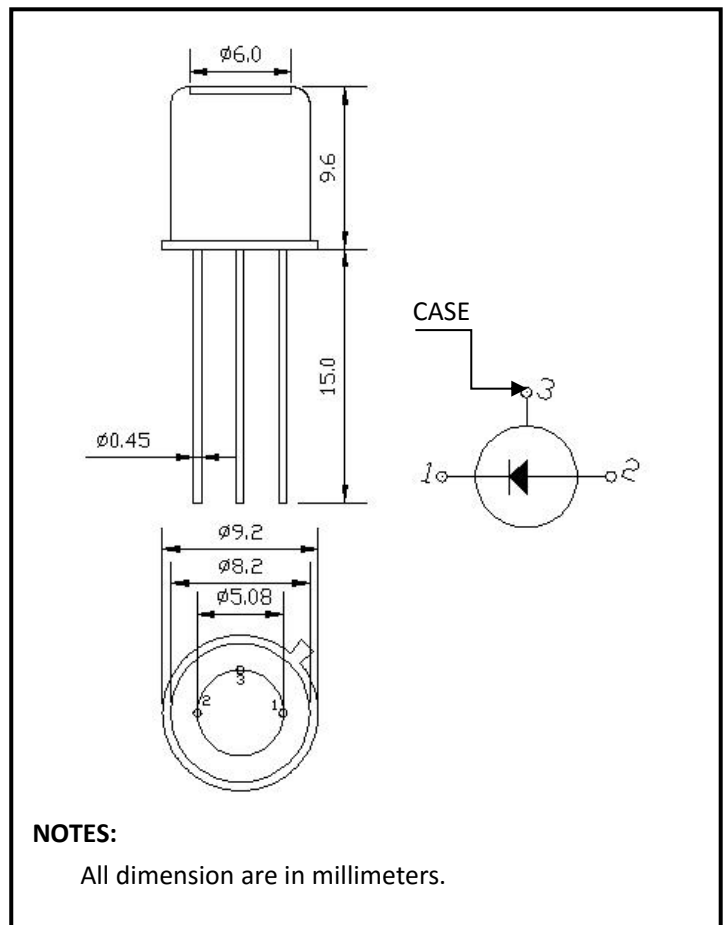
- \* High sensitivity response
- \* Wide angular response
- \* High reliability in demanding environments
- \* Operating temperature is from -40 to +100°C
- \* Storage temperature is from -40 to +100°C

## General Ratings

- \* Type Silicon Photodiode
- \* Similar to S2684-254
- \* Chip active area: 4.3\*4.3mm
- \* Low dark current

## Applications

- \* UV detect
- \* Optical measurement equipment
- \* Analytical/medical Instrument
- \* Pollution monitoring

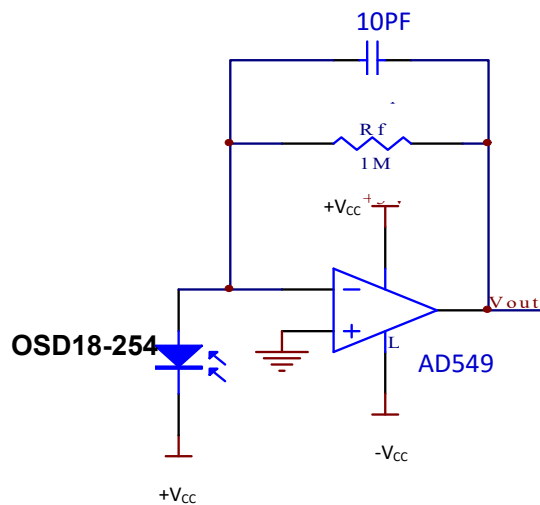


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## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Dark current	$I_D$	$V_R=10\text{mV}$		0.2		nA
		$V_R=10\text{V}$		3.5		
Tempcoefficient of $I_D$	$T_{CID}$			0.18		times/°C
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu\text{A}$ $E_v=0\text{lx}$			60	V
Junction Capacitance	$C_j$	$V_R=0\text{V}$ $f=1\text{MHz}$		480		pF
		$V_R=10\text{V}$ $f=1\text{MHz}$		72		
Photo sensitivity	$S_R$	254nm		0.02		A/W
Spectral Application Range	$\lambda_{\text{range}}$		240		270	nm
Spectral Response-Peak	$\lambda_p$			254		nm
Shunt resistance	$R_{sh}$	$V_R=10\text{mV}$		0.5		GΩ
Rsh Temperature Coefficient	$TC_{Rsh}$			0.18		%/°C
Angular Resp 50% Resp Pt	$\theta_{1/2}$			$\pm 55$		Degrees
Noise Equivalent Power	NEP	$V_R=10\text{V}$ $\lambda=254\text{nm}$		$1.86 \times 10^{-16}$		W/Hz <sup>1/2</sup>
Specific Detectivity	$D^*$	$V_R=10\text{V}$ $\lambda=254\text{nm}$		$2.31 \times 10^{16}$		cm(Hz/W) <sup>1/2</sup>

## Typical application circuit



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OTRON ELECTRONIC TECHNOLOGY CO.LTD

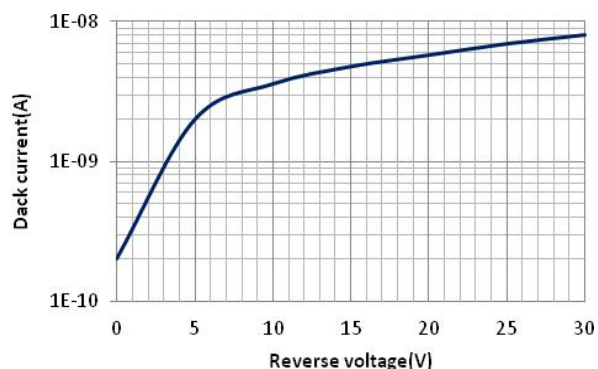
TEL:+86-21-54971821

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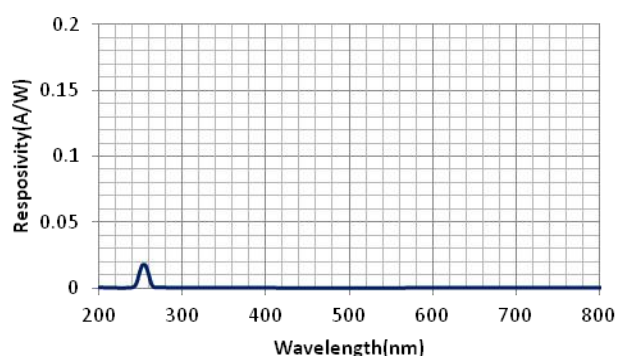
EMAIL: frank.shuai@e-otron.com

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## ■ Dark current vs. reverse voltage

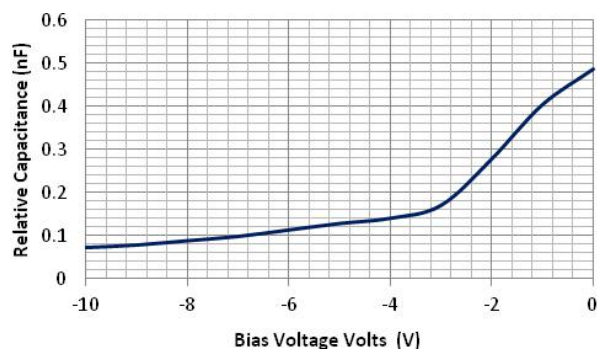


## ■ Spectral response



## ■ Relative Junction Capacitance

VS. Voltage



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